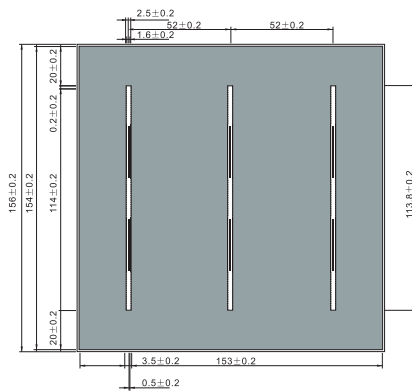
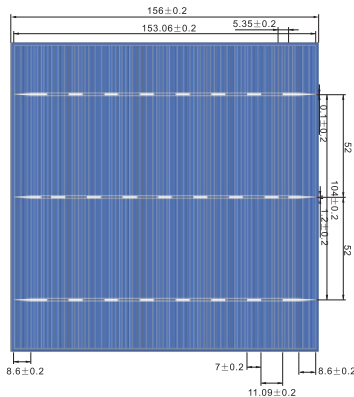


156mm × 156mm Polycrystalline Silicon Cell



Mechanical Data And Design

Format	156mm × 156mm ± 0.5mm
Thickness(Wafer)	200μm±20μm
Front (-)	3 × 1.2 ± 0.2mm busbars(silver), Blue anti-reflection coating(silicon nitride)
Back (+)	3 × 1.6 ± 0.2mm wide soldering pads(silver), Back surface field(aluminium)

Temperature Coefficients

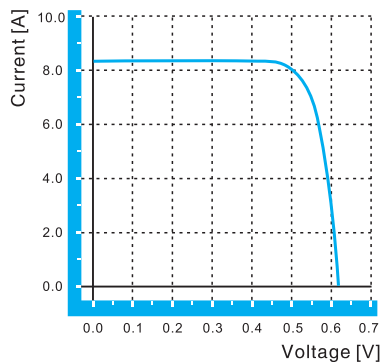
TkVoltage	-0.32%/K
TkCurrent	+0.06%/K
TkPower	-0.44%/K

Electrical Characteristics

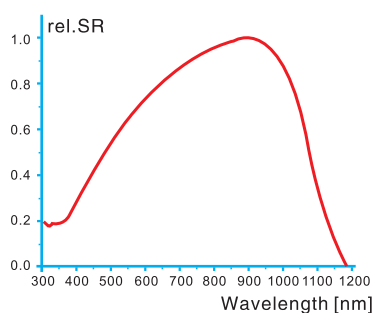
Efficiency (%)	Pmpp (W)	Umpp (V)	Impp (A)	Uoc (V)	Isc (A)	FF(%)
17.80-18.00	4.33	0.53	8.17	0.635	8.693	78.44
17.60-17.80	4.29	0.526	8.156	0.632	8.668	78.31
17.40-17.60	4.24	0.522	8.123	0.629	8.615	78.25
17.20-17.40	4.19	0.52	8.058	0.625	8.576	78.17
17.00-17.20	4.14	0.518	7.992	0.623	8.524	77.96
16.80-17.00	4.09	0.517	7.911	0.62	8.473	77.86
16.60-16.80	4.04	0.513	7.875	0.618	8.413	77.7
16.40-16.60	3.99	0.511	7.808	0.617	8.344	77.5
16.20-16.40	3.94	0.506	7.787	0.614	8.284	77.46
16.00-16.20	3.89	0.504	7.718	0.612	8.221	77.31

All electrical data measured under standard test conditions: 1000W/m², AM 1.5, 25°C.

IV Curve



Spectral Response



Intensity Dependence

Intensity (W/m ²)	Isc (mA)	Voc (mV)
1000	1	1
900	0.9	0.996
500	0.5	0.968
300	0.3	0.942
200	0.2	0.92

Ratio of Voc(Isc) at reduced induced intensity to Voc(Isc) at 1000W/m²